

SPECIFICATION

DEVICE NAME : Power MOSFET

TYPE NAME : 2SK2052-R

SPEC. No. :

Fuji Electric Co.,Ltd.

This Specification is subject to change without notice.

	DATE	NAME	APPROVED	Fuji Electric Co.,Ltd.	
DRAWN				DWG.NO.	1/10
CHECKED					

1. Scope
This specifies Fuji power MOSFET 2SK2052-R
2. Construction N-channel enhancement mode power MOSFET
3. Application for switching
4. Outview TO-3PF Outview See to 4/10 page
5. Absolute maximum ratings at $T_c=25^\circ\text{C}$ (unless otherwise specified)

Description	Symbol	Characteristics	Unit	Remarks
Drain-source voltage	V_{DS}	500	V	
Drain-gate voltage	V_{DGR}	500	V	$R_{GS}=20\text{K}\Omega$
Continuous Drain current	I_D	± 10	A	
Pulsed drain current	I_{Dpulsa}	± 40	A	
Gate-source voltage	V_{GS}	± 20	V	
Maximum power dissipation	P_D	80	W	
Operating and storage temperature range	T_{ch}	150	$^\circ\text{C}$	
	T_{sto}	-55 ~ +150	$^\circ\text{C}$	

6. Electrical characteristics at $T_c=25^\circ\text{C}$ (unless otherwise specified)
Static ratings

Description	Symbol	Conditions	Characteristics			Unit
			Min.	Typ.	Max.	
Drain-source breakdown voltage	BV_{DSS}	$I_D=1\text{mA}$ $V_{GS}=0\text{V}$	500			V
Gate threshold voltage	$V_{GS(th)}$	$I_D=10\text{mA}$ $V_{DS}=V_{GS}$	2.1	3.0	4.0	V
Zero gate voltage drain current	I_{DSS}	$V_{DS}=500\text{V}$ $V_{GS}=0\text{V}$	$T_{ch}=25^\circ\text{C}$	10	500	μA
	I_{DSS}		$T_{ch}=125^\circ\text{C}$	0.5	2.0	mA
Gate-source leakage current	I_{GSS}	$V_{GS}=\pm 20\text{V}$ $V_{DS}=0\text{V}$		10	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$I_D=5\text{A}$ $V_{GS}=10\text{V}$		0.80	1.10	Ω

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Dynamic ratings

Description	Symbol	Conditions	Characteristics			Unit
			Min.	Typ.	Max.	
Forward transconductance	g_{fs}	$I_D = 5\text{ A}$ $V_{DS} = 25\text{ V}$	4	8		S
Input capacitance	C_{iss}	$V_{DS} = 25\text{ V}$ $V_{GS} = 0\text{ V}$ $f = 1\text{ MHz}$		1100	1600	pF
Output capacitance	C_{oss}			140	210	pF
Reverse transfer capacitance	C_{rss}			75	110	pF
Turn-on time	$t_{d(on)}$	$V_{CC} = 300\text{ V}$ $V_{GS} = 10\text{ V}$ $I_D = 10\text{ A}$ $R_{GS} = 25\ \Omega$		25	40	ns
	t_r			60	90	ns
Turn-off time	$t_{d(off)}$			200	300	ns
	t_f			90	140	ns

Reverse diode

Description	Symbol	Conditions	Characteristics			Unit
			Min.	Typ.	Max.	
Diode forward on-voltage	V_{SD}	$I_F = I_{DR}$ $V_{GS} = 0\text{ V}$, $T_{ch} = 25^\circ\text{C}$		0.95	1.8	V
Reverse recovery time	t_{rr}	$I_F = I_{DR}$ $V_{GS} = 0\text{ V}$ $-di_F/dt = 100\text{ A}/\mu\text{s}$ $T_{ch} = 25^\circ\text{C}$		150	200	ns
Reverse recovery charge	Q_{rr}			0.75		μC

7. Thermal resistance

Description	Symbol	Conditions	Characteristics			Unit
			Min.	Typ.	Max.	
Thermal resistance	$R_{th_{ch-c}}$				1.56	$^\circ\text{C}/\text{W}$
	$R_{th_{ch-a}}$				30	$^\circ\text{C}/\text{W}$

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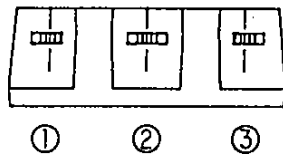
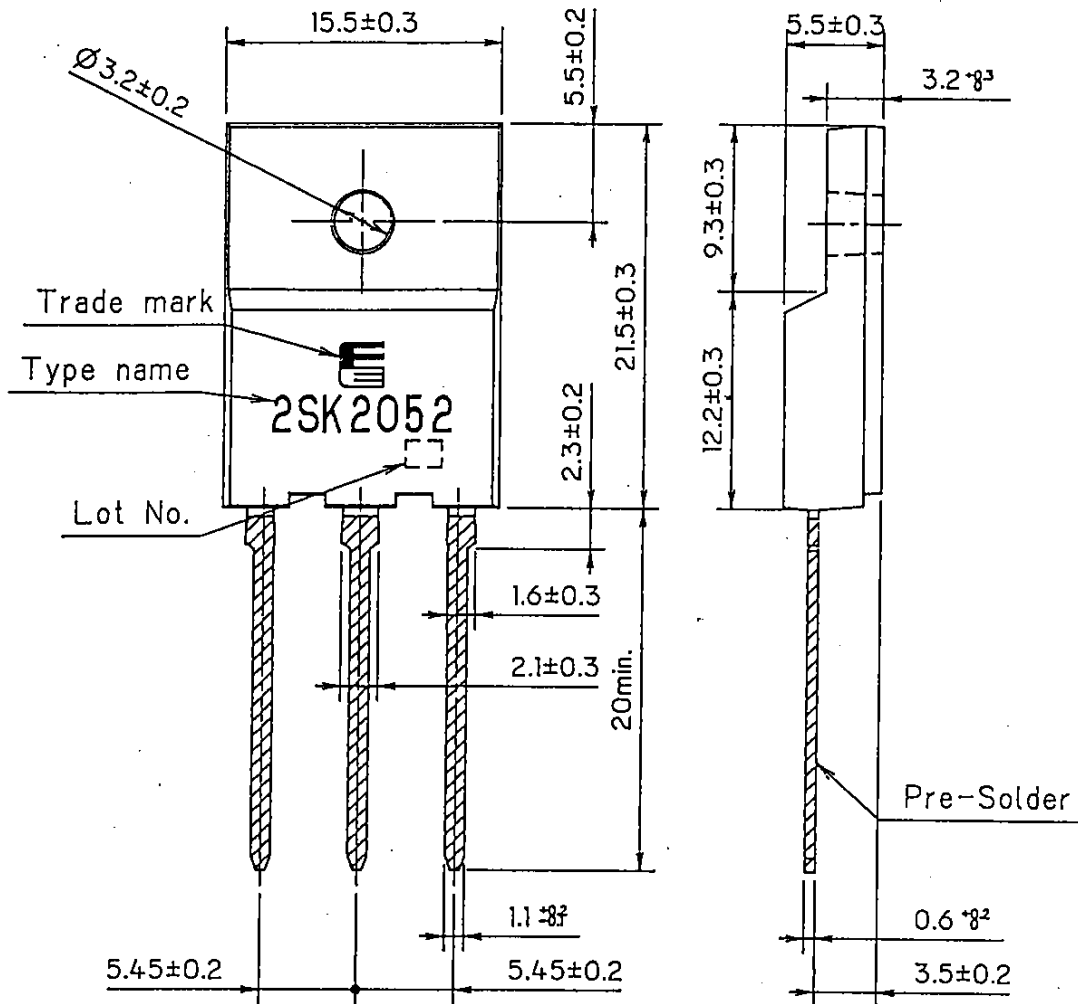
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FUJI POWER MOSFET

TYPE : 2SK2052-R



CONNECTION

- ① GATE
- ② DRAIN
- ③ SOURCE

DIMENSIONS ARE IN MILLIMETERS.

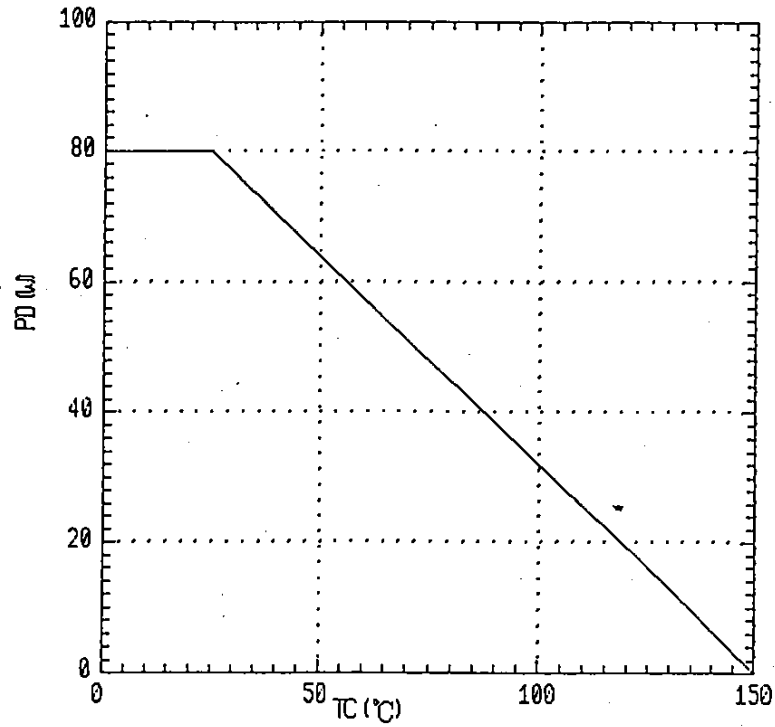
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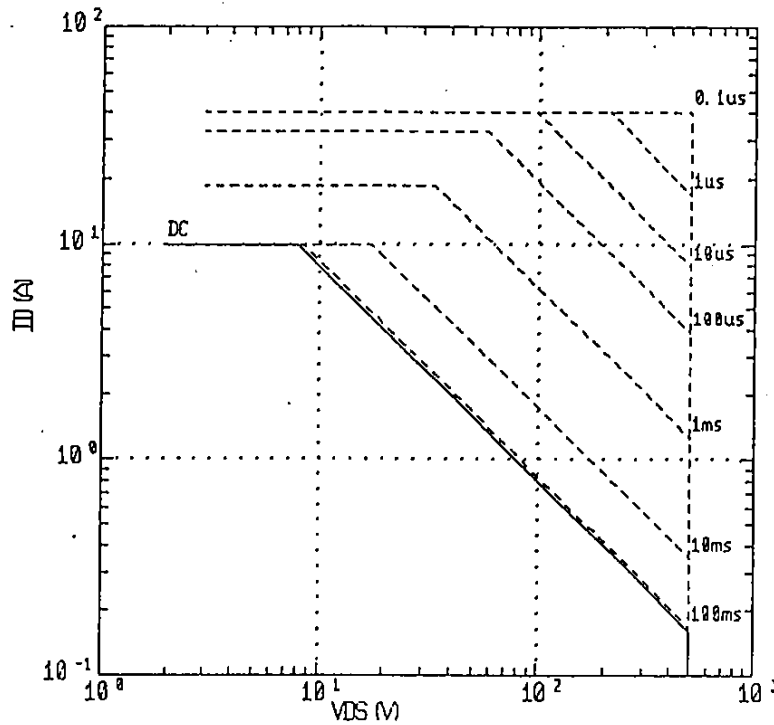
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Power Dissipation
 $PD=f(TC)$



Safe operating area
 $ID=f(VDS): D=0.01, Tc=25^{\circ}C$



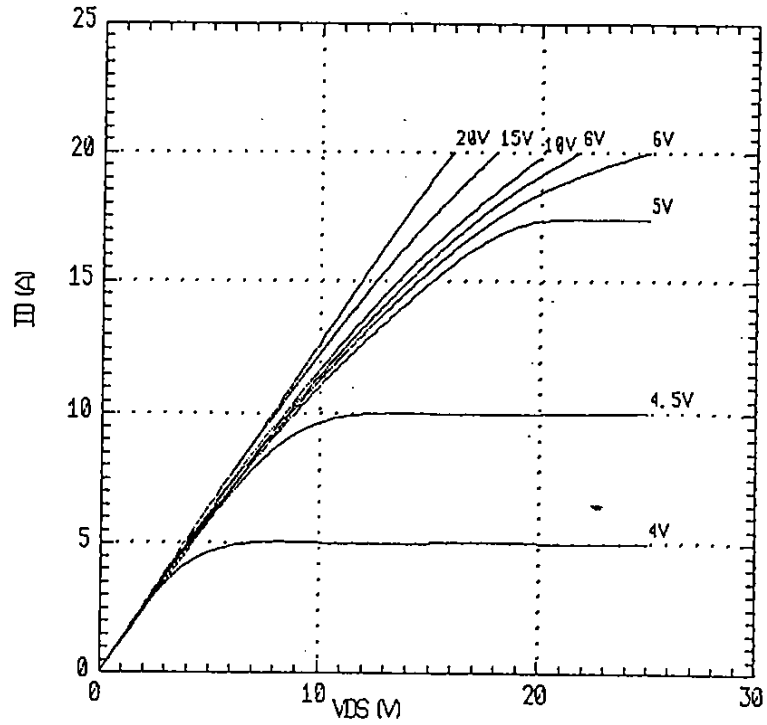
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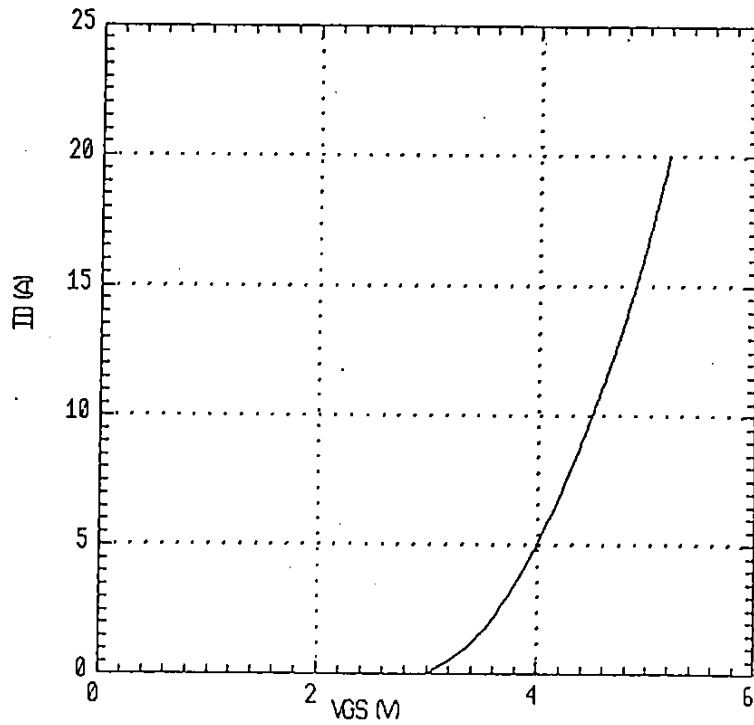
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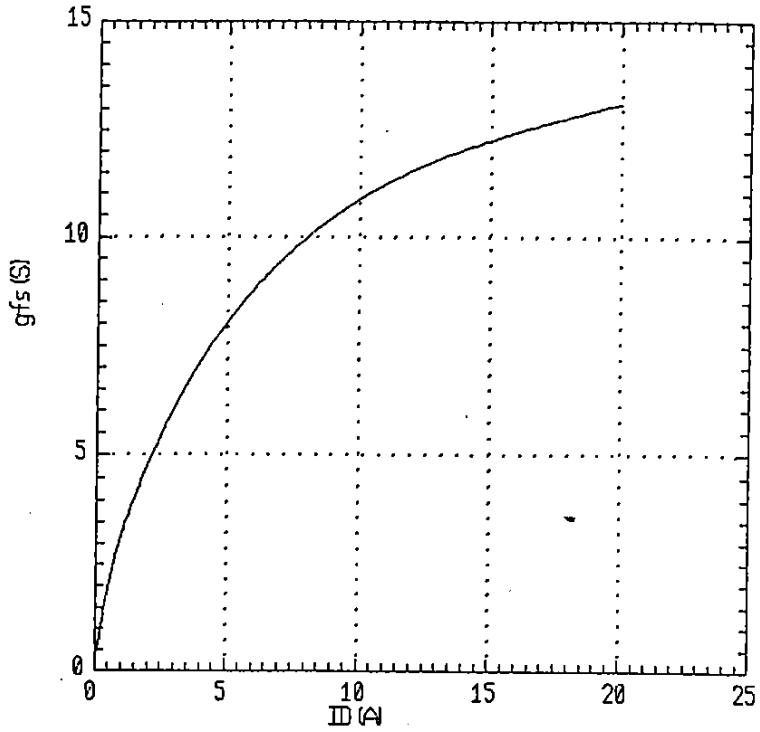
Typical output characteristics
 $I_D = f(V_{DS})$: 80 μ s pulse test, $T_{ch} = 25^\circ\text{C}$



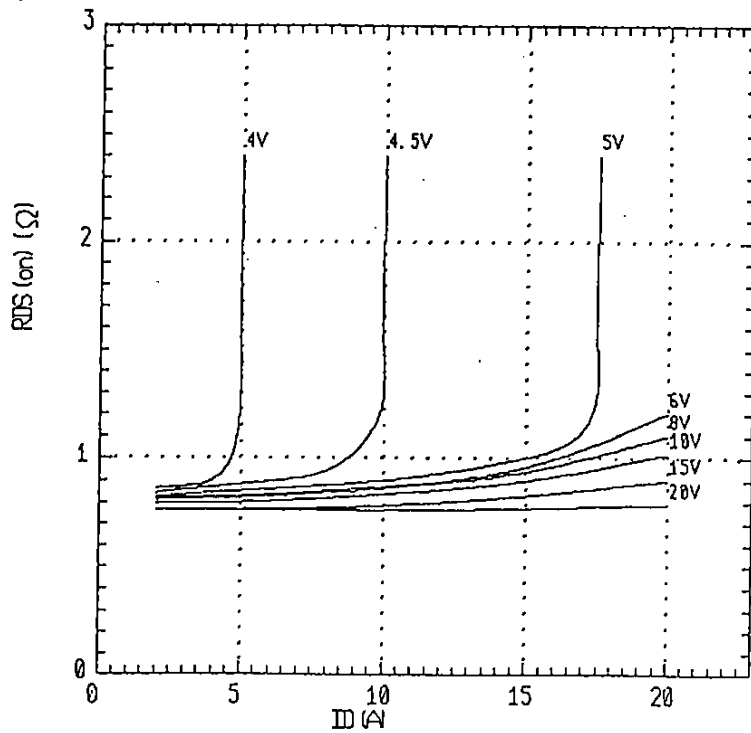
Typical Transfer Characteristic
 $I_D = f(V_{GS})$: 80 μ s pulse test, $V_{DS} = 25\text{V}$, $T_{ch} = 25^\circ\text{C}$



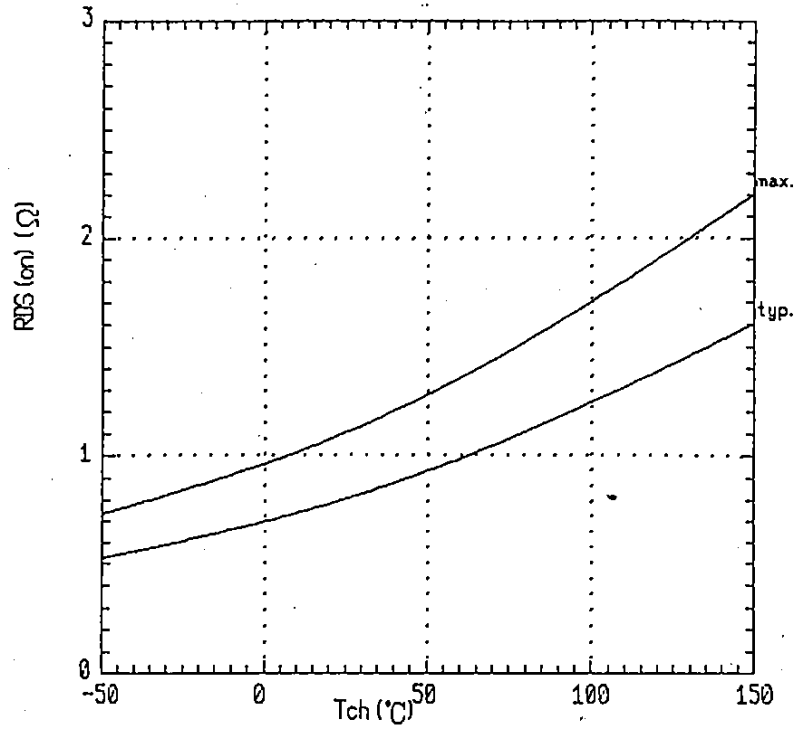
Typical Transconductance
 $g_{fs}=f(I_D): 80\mu s$ pulse test, $V_{DS}=25V, T_{ch}=25^\circ C$



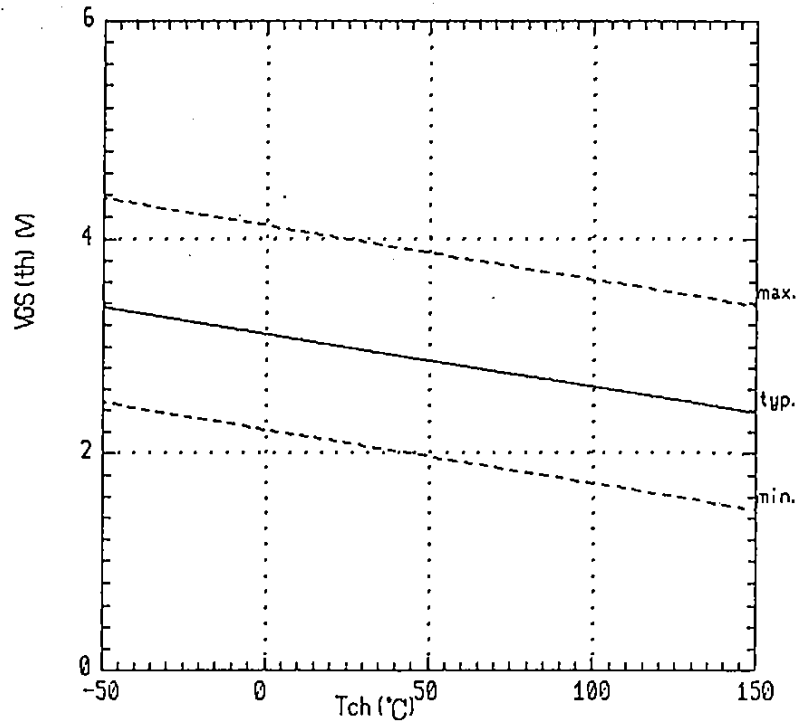
Typical Drain-source on-state resistance
 $R_{DS(on)}=f(I_D): 80\mu s$ pulse test, $T_{ch}=25^\circ C$



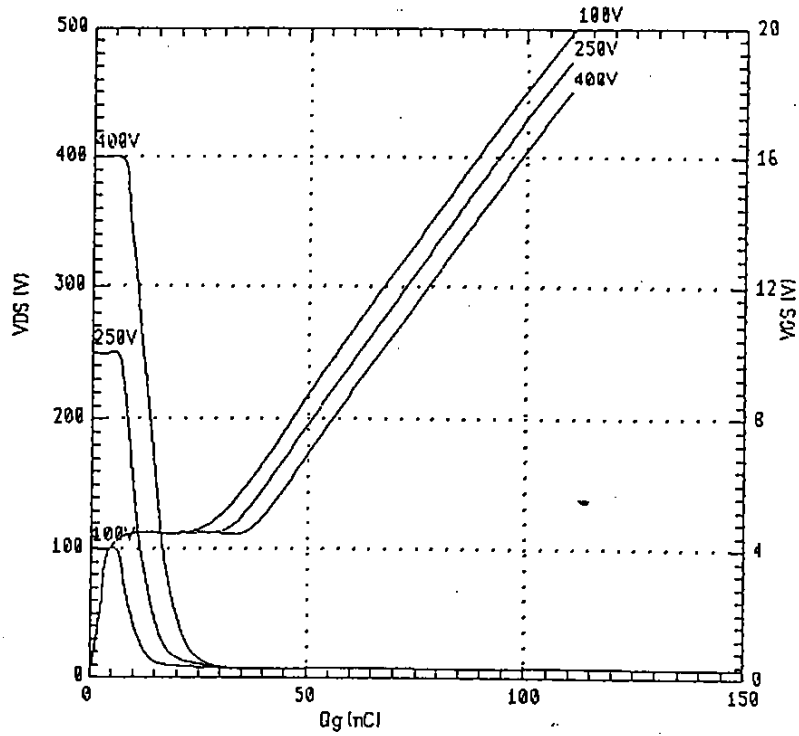
Drain-source on-state resistance
 $R_{DS(on)} = f(T_{ch}) : I_D = 5A, V_{GS} = 10V$



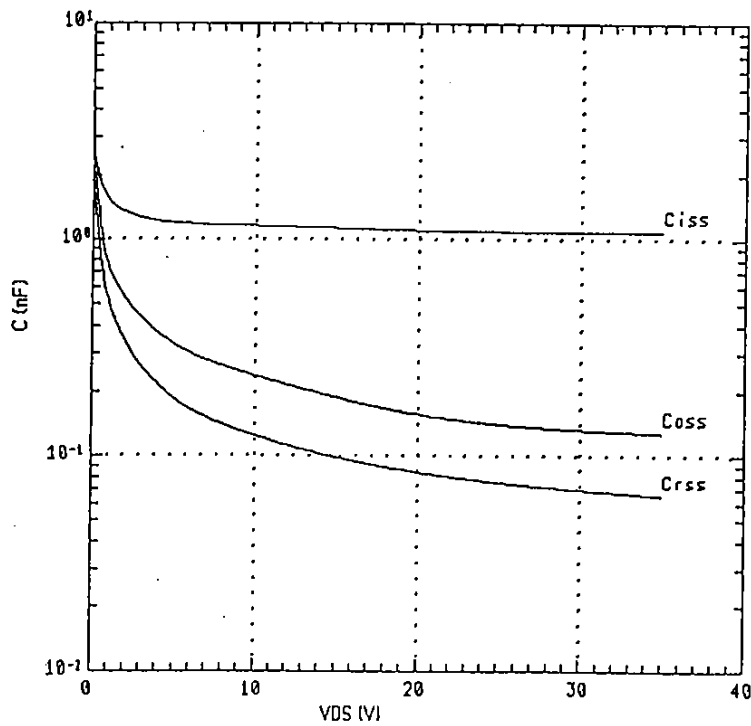
Gate threshold voltage
 $V_{GS(th)} = f(T_{ch}) : V_{DS} = V_{GS}, I_D = 10mA$



Typical gate charge characteristics
 $V_{GS} = f(Q_g) : I_D = 10A$



Typical capacitances
 $C = f(V_{DS}) : V_{GS} = 0V, f = 1MHz$



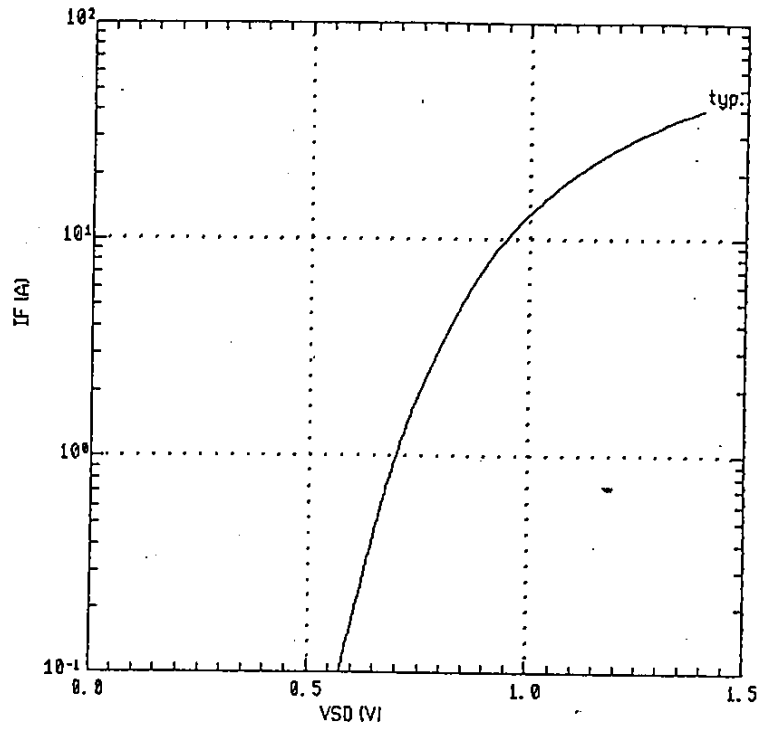
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Forward characteristic of reverse diode
 $I_F = f(V_{SD}) : 80 \mu s$ pulse test, $T_{ch} = 25^\circ C$



Transient thermal impedance $Z_{thch-c} = f(t)$ parameter: $D = t/T$

